

N-channel 30 V, 6.6 mΩ logic level MOSFET in LFPAK33

19 September 2016

Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	30	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	70	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	75	W
Static charact	eristics	·	1	1			
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 20 A; T _j = 25 °C; <u>Fig. 11</u>		-	5.5	6.6	mΩ
Dynamic char	acteristics						
Q _{GD}	gate-drain charge	$I_D = 20 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$		-	7.8	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D
2	S	Source		
3	S	Source	\bigcirc	G-UF4
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Cable 3. Ordering information							
Type number	Package	e					
	Name	Description	Version				
BUK9M6R6-30E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9M6R6-30E	96E630

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	30	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	75	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	70	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	54.7	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3		-	309	А

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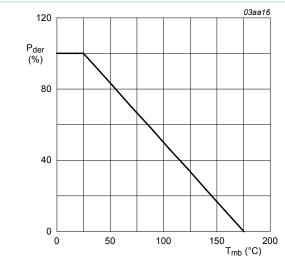
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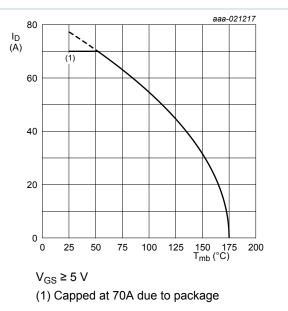
Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C		-	62.5	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	309	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 70 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3][4]	-	53	mJ

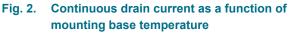
- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
- [2] Significantly longer life times are achieved by lowering T_i and or V_{GS}
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



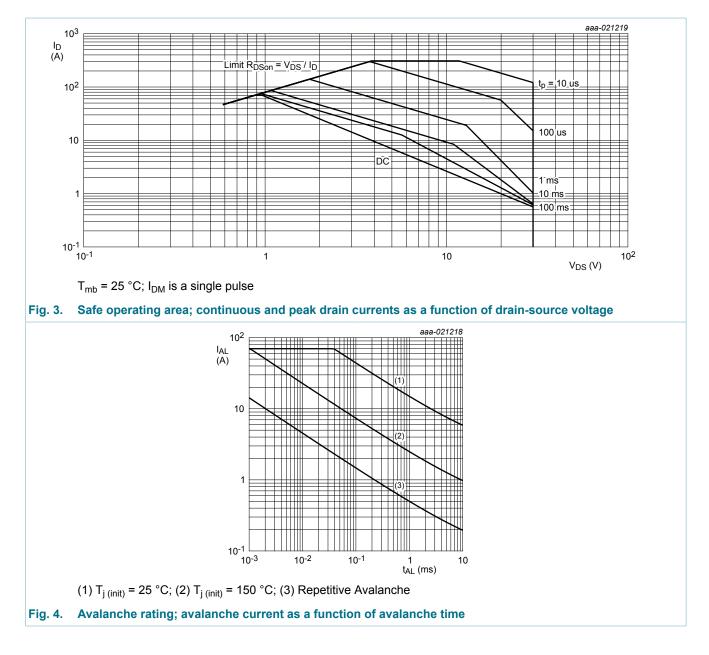


$$I_D = 77A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

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9. Thermal characteristics

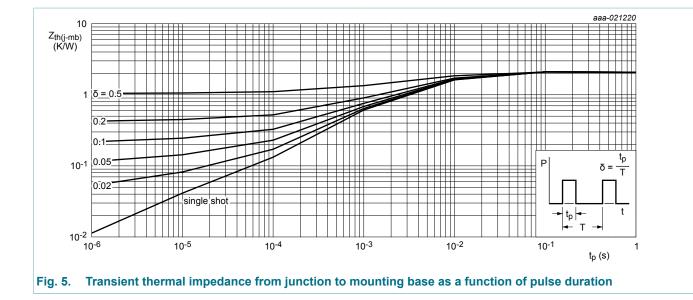
Table 6. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	_	1.82	2	K/W

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10. Characteristics

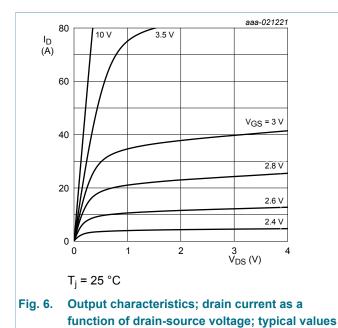
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·	I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
breakdown voltage	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.45	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 20 A; T _j = 25 °C; <u>Fig. 11</u>	-	5.5	6.6	mΩ
	resistance	V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; Fig. 11	-	4.4	5.3	mΩ
		V _{GS} = 5 V; I _D = 20 A; T _j = 175 °C; Fig. 12	-	-	13	mΩ
Dynamic ch	naracteristics	· · ·	1		1	
Q _{G(tot)}	total gate charge	I_D = 20 A; V_{DS} = 24 V; V_{GS} = 5 V; T _j = 25 °C	-	18	-	nC

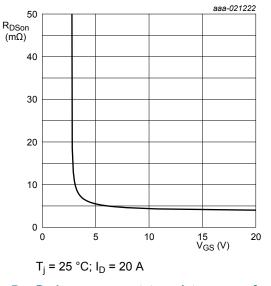
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Symbol	Parameter	Conditions	r	Min	Тур	Max	Unit
Q _{GS}	gate-source charge	I_D = 20 A; V_{DS} = 24 V; V_{GS} = 5 V;	-	-	3.9	-	nC
Q _{GD}	gate-drain charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	-	7.8	-	nC
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;	-	-	1505	2001	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	-	290	348	pF
C _{rss}	reverse transfer capacitance	-		-	179	245	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 25 V; R_L = 1 \Omega; V_{GS} = 5 V;$ $R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	-	10.2	-	ns
t _r	rise time		-	-	26.8	-	ns
t _{d(off)}	turn-off delay time		-	-	23.9	-	ns
t _f	fall time		-	-	22.3	-	ns
Source-dra	ain diode				I	1	
V _{SD}	source-drain voltage	I_{S} = 20 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V;		-	20	-	ns
Q _r	recovered charge	V _{DS} = 20 V; T _j = 25 °C	-	_	10.6	-	nC

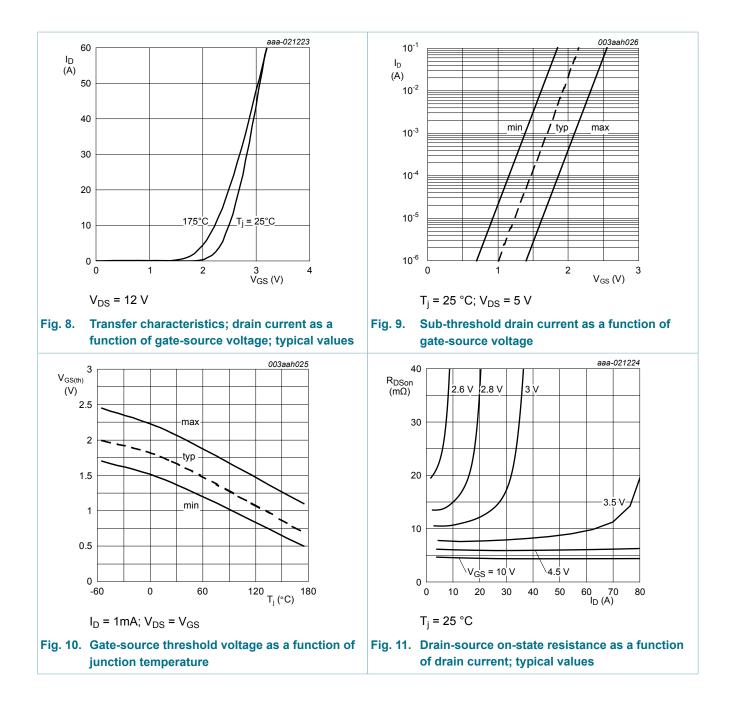






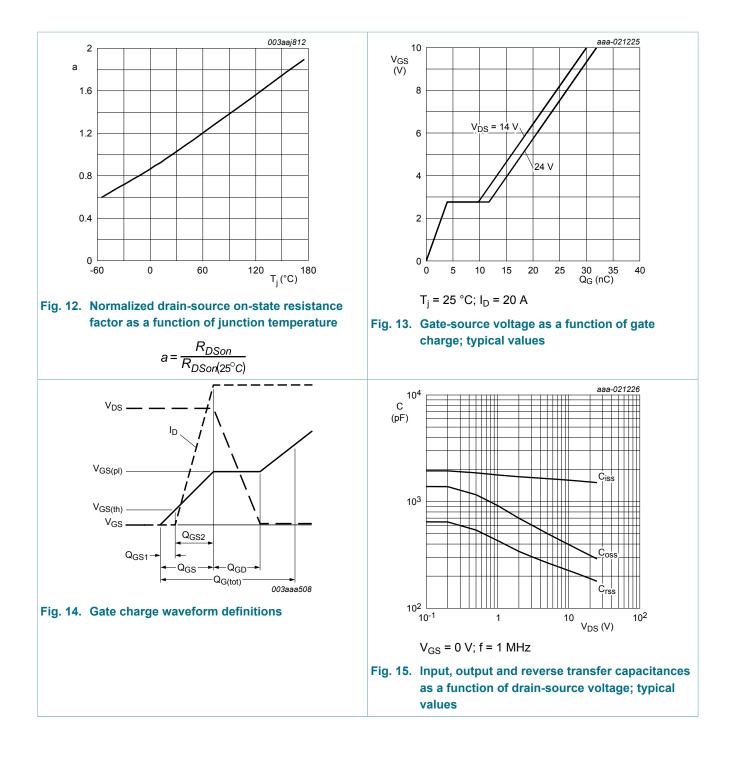
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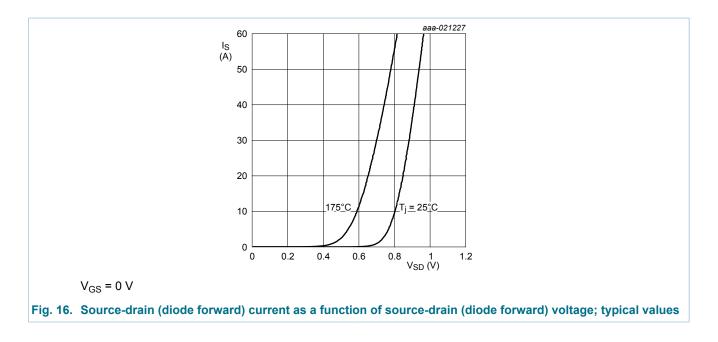
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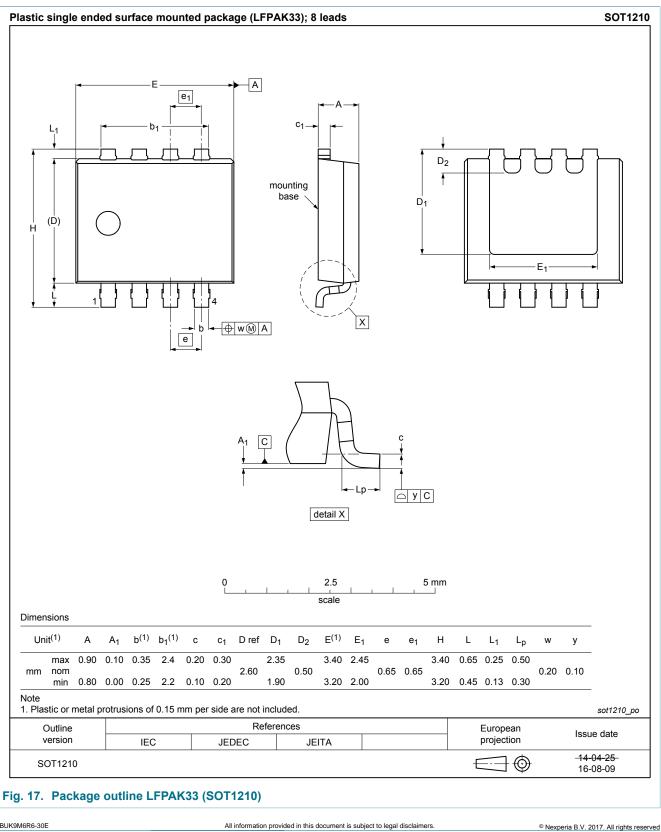


11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

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12. Package outline



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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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